

GMBT1036 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

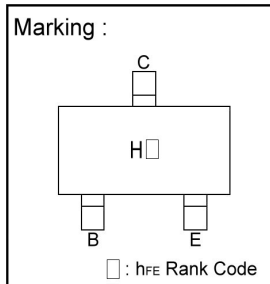
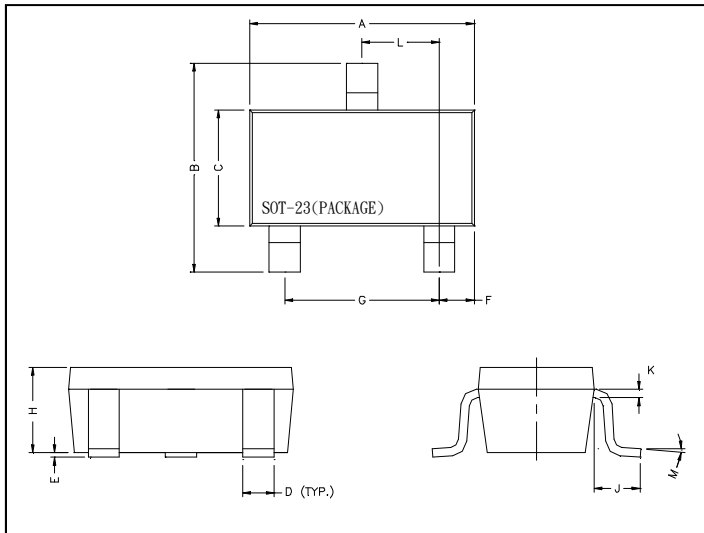
Description

The GMBT1036 is designed for medium power amplifier applications.

Features

- $I_{CMax.} = -500mA$
- Low $V_{CE(sat)}$. Optimal for low voltage operation.
- Complementary to GMBT2411

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55~+150	$^\circ C$
Collector to Base Voltage	V_{CB0}	-40	V
Collector to Emitter Voltage	V_{CE0}	-32	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-500	mA
Total Power Dissipation	PD	225	mW

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise stated)

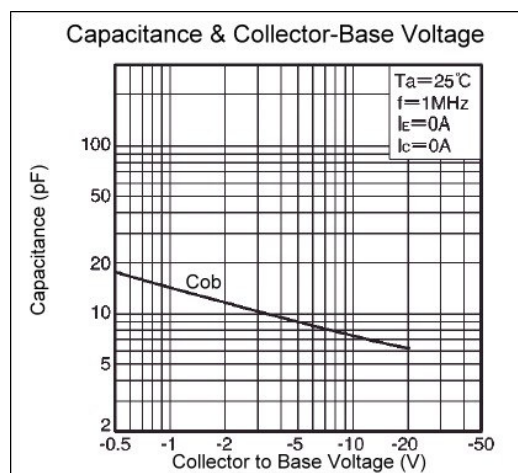
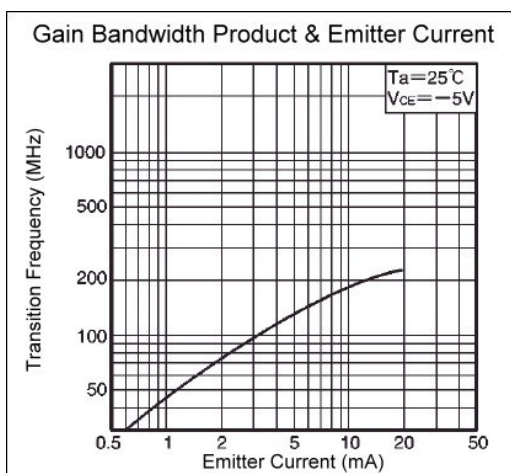
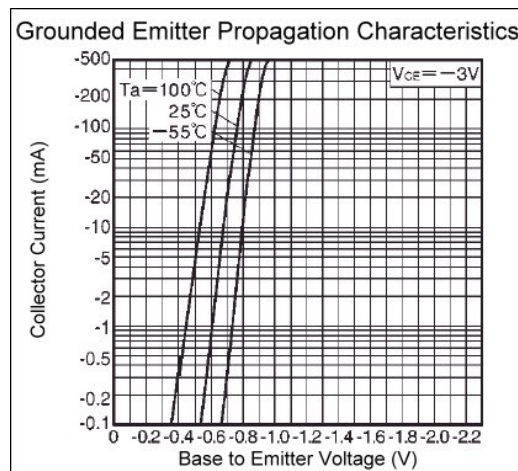
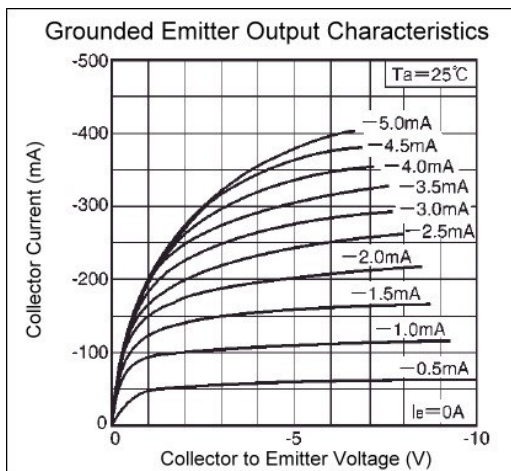
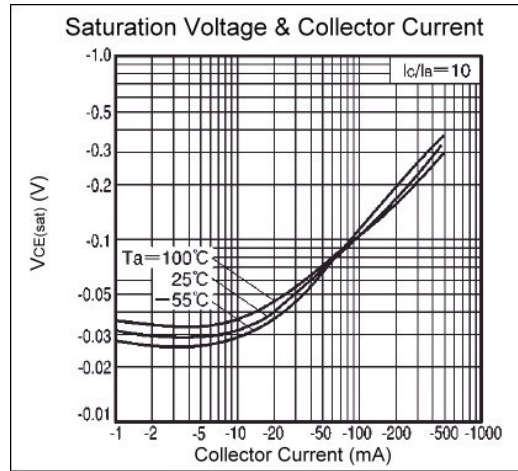
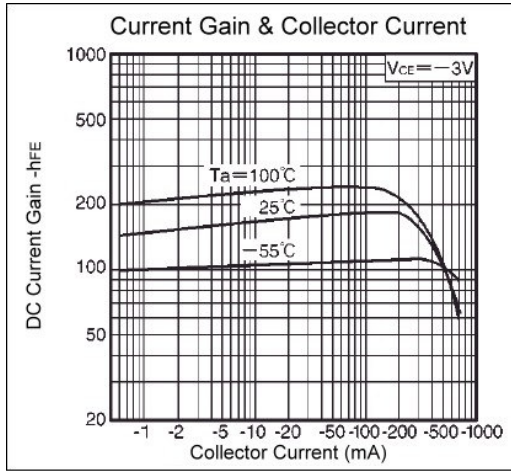
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CB0}	-40	-	-	V	$I_C = -100\mu A, I_E = 0$
BV_{CE0}	-32	-	-	V	$I_C = -1mA, I_B = 0$
BV_{EB0}	-5	-	-	V	$I_E = -100\mu A, I_C = 0$
I_{CBO}	-	-	-1	μA	$V_{CB} = -20V, I_E = 0$
I_{EBO}	-	-	-1	μA	$V_{EB} = -4V, I_C = 0$
* $V_{CE(sat)}$	-	-	-400	mV	$I_C = -100mA, I_B = -10mA$
*hFE	82	-	390		$V_{CE} = -3V, I_C = -10mA$
fT	-	200	-	MHz	$V_{CE} = -5V, I_E = 20mA, f = 100MHz$
Cob	-	7	-	pF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

*Measured under pulse condition. Pulse width=300 μs , Duty Cycle $\leq 2\%$

Classification Of hFE

Rank	HP	HQ	HR
Range	82 - 180	120 - 270	180 - 390

Characteristics Curve



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